

## Product Overview

### FFSH40120A: SiC Schottky Diode, 1200 V, 40 A

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

### Features

- Max Junction Temperature 175 °C
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

### Applications

- PFC
- Industrial Power
- Solar
- EV Charger
- UPS

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Device Grade	Configuration	V <sub>RRM</sub> (V)	I <sub>F(ave)</sub> (A)	V <sub>F</sub> (Max)	I <sub>FSM</sub> (A)	I <sub>R</sub> (Max) (μA)	Package Type
FFSH40120A	13.4042	Pb-free Halide free	Active	Commercial	Single	1200	40	1.75			TO-247-2

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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